



STD4N52K3, STF4N52K3 STP4N52K3, STU4N52K3

N-channel 525 V, 2.5 A, 2.1 Ω IPAK, DPAK, TO-220FP, TO-220
SuperMESH3™ Power MOSFET

Features

Order codes	V _{DSS}	R _{DS(on)} max	I _D	P _w
STD4N52K3	525 V	< 2.6 Ω	2.5 A	45 W
STF4N52K3			2.5 A	20 W
STP4N52K3			2.5 A ⁽¹⁾	45 W
STU4N52K3			2.5 A	45 W

1. Limited by package

- 100% avalanche tested
- Extremely high dv/dt capability
- Gate charge minimized
- Very low intrinsic capacitance
- Improved diode reverse recovery characteristics
- Zener-protected

Application

Switching applications

Description

These devices are made using the SuperMESH3™ Power MOSFET technology that is obtained via improvements applied to STMicroelectronics' SuperMESH™ technology combined with a new optimized vertical structure. The resulting product has an extremely low on resistance, superior dynamic performance and high avalanche capability, making it especially suitable for the most demanding applications.

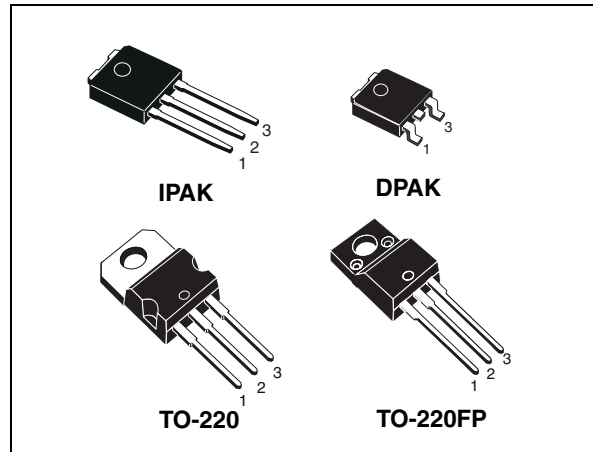


Figure 1. Internal schematic diagram

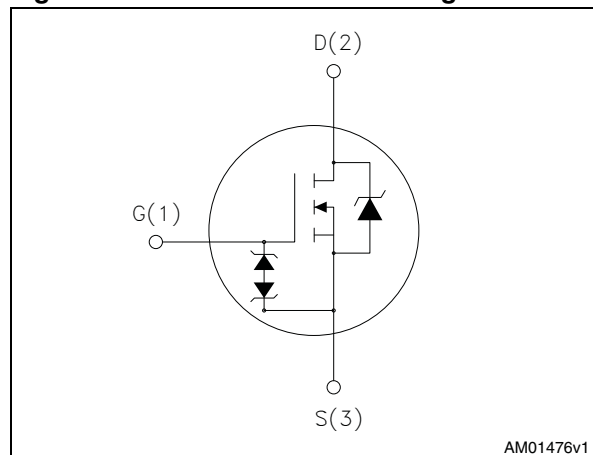


Table 1. Device summary

Order codes	Marking	Package	Packaging
STD4N52K3	4N52K3	IPAK	Tube
STF4N52K3	4N52K3	DPAK	Tape and reel
STP4N52K3	4N52K3	TO-220FP	Tube
STU4N52K3	4N52K3	TO-220	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value				Unit
		TO-220	DPAK	IPAK	TO-220FP	
V _{DS}	Drain-source voltage (V _{GS} = 0)	525				V
V _{GS}	Gate- source voltage	± 30				V
I _D	Drain current (continuous) at T _C = 25 °C	2.5		2.5 ⁽¹⁾		A
I _D	Drain current (continuous) at T _C = 100 °C	2		2 ⁽¹⁾		A
I _{DM} ⁽²⁾	Drain current (pulsed)	10		10 ⁽¹⁾		A
P _{TOT}	Total dissipation at T _C = 25 °C	45		20		W
I _{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T _j max)	1.3				A
E _{AS}	Single pulse avalanche energy (starting T _j = 25°C, I _D = I _{AR} , V _{DD} = 50V)	110				mJ
dv/dt ⁽³⁾	Peak diode recovery voltage slope	12				V/ns
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s; T _C = 25 °C)				2500	V
T _{stg}	Storage temperature	-55 to 150				°C
T _j	Max. operating junction temperature	150				°C

1. Limited by package

2. Pulse width limited by safe operating area

3. $I_{SD} \leq 2.5\text{ A}$, $di/dt = 400\text{ A}/\mu\text{s}$, peak $V_{DD} \leq V_{(BR)DSS}$, $V_{DD} = 80\% V_{(BR)DSS}$.

Table 3. Thermal data

Symbol	Parameter	Value				Unit
		TO-220	DPAK	IPAK	TO-220FP	
$R_{thj-case}$	Thermal resistance junction-case max	2.78		6.25		$^{\circ}\text{C}/\text{W}$
$R_{thj-pcb}$ ⁽¹⁾	Thermal resistance junction-pcb max		50			$^{\circ}\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	62.5		100	62.5	$^{\circ}\text{C}/\text{W}$
T_l	Maximum lead temperature for soldering purpose	300		300		$^{\circ}\text{C}$

1. When mounted on 1inch sq FR-4 board, 2 oz Cu

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 4. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$, $V_{GS} = 0$	525			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$ $V_{DS} = \text{Max rating}$, $T_C = 125\text{ °C}$			1 50	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 50\text{ }\mu\text{A}$	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 1.25\text{ A}$		2.1	2.6	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	334 28 5	-	pF pF pF
$C_{oss(eq)}^{(1)}$	Equivalent output capacitance time related	$V_{DS} = 0\text{ to }420\text{ V}$, $V_{GS} = 0$	-	20	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	4	-	Ω
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 400\text{ V}$, $I_D = 2.5\text{ A}$, $V_{GS} = 10\text{ V}$ (see Figure 19)	-	11 2 7	-	nC nC nC

1. $C_{oss\ eq.}^{(1)}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 260\text{ V}$, $I_D = 1.25\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 18)	-	8	-	ns
t_r	Rise time			7		ns
$t_{d(off)}$	Turn-off-delay time			21		ns
t_f	Fall time			14		ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		2.5	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				10	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 2.5\text{ A}$, $V_{GS} = 0$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 2.5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$ (see Figure 23)	-	173		ns
Q_{rr}	Reverse recovery charge			778		nC
I_{RRM}	Reverse recovery current			9		A
t_{rr}	Reverse recovery time	$I_{SD} = 2.5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 23)	-	196		ns
Q_{rr}	Reverse recovery charge			941		nC
I_{RRM}	Reverse recovery current			10		A

1. Pulse width limited by safe operating area

2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%

Table 8. Gate-source Zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$BV_{GSO}^{(1)}$	Gate-source breakdown voltage	$I_{gs} = \pm 1\text{ mA}$ (open drain)	30	-		V

1. The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220

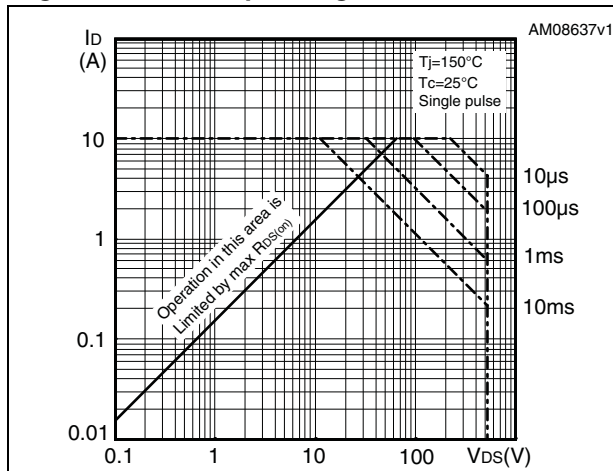


Figure 3. Thermal impedance for TO-220

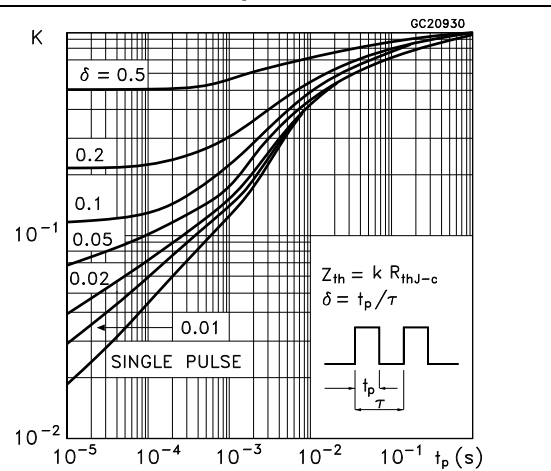


Figure 4. Safe operating area for TO-220FP

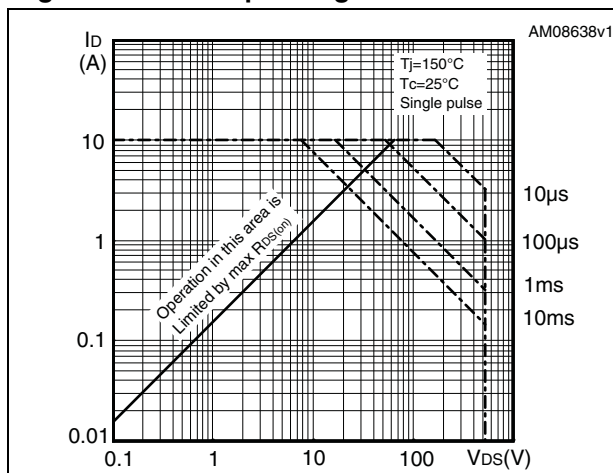


Figure 5. Thermal impedance for TO-220FP

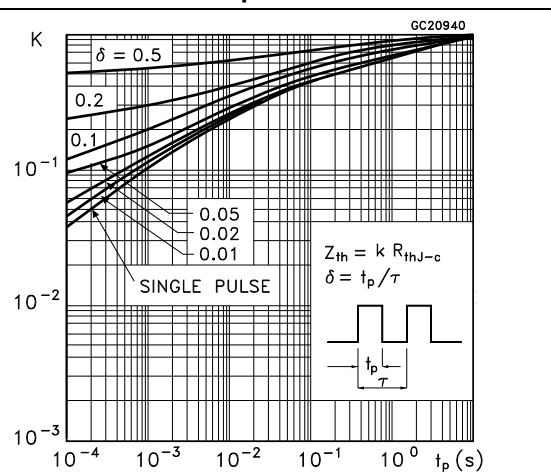


Figure 6. Safe operating area for DPAK, IPAK

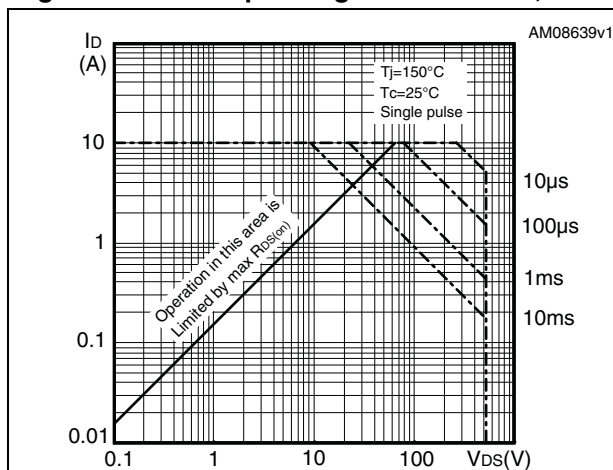


Figure 7. Thermal impedance for DPAK, IPAK

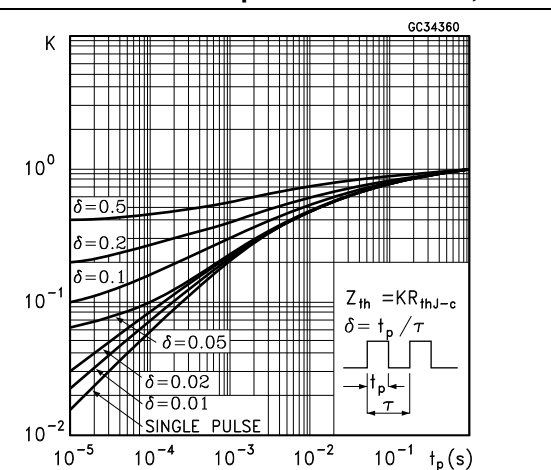


Figure 8. Output characteristics

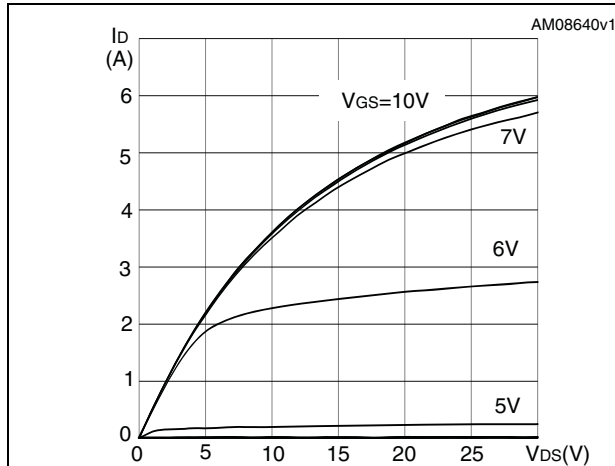


Figure 9. Transfer characteristics

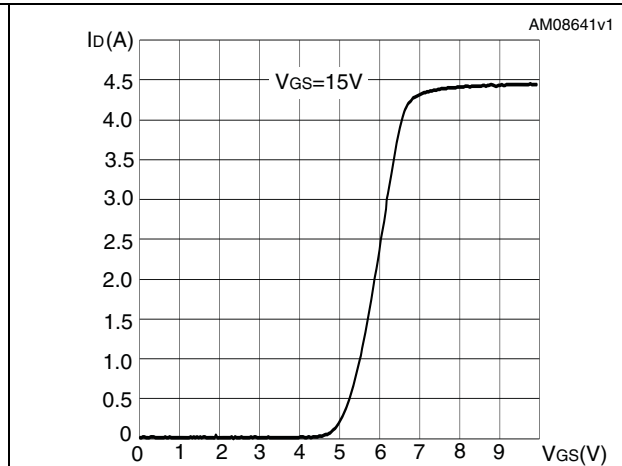
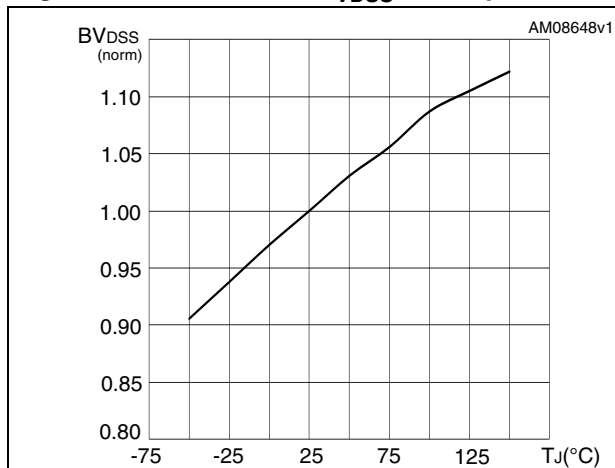
Figure 10. Normalized $B_{V_{DS}}$ vs temperature

Figure 11. Static drain-source on resistance

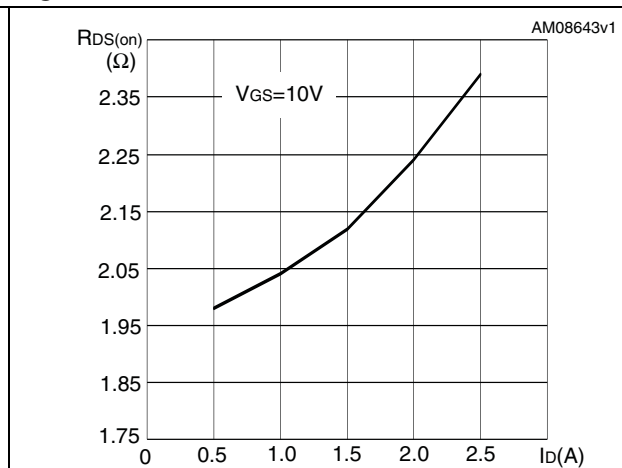


Figure 12. Capacitance variations

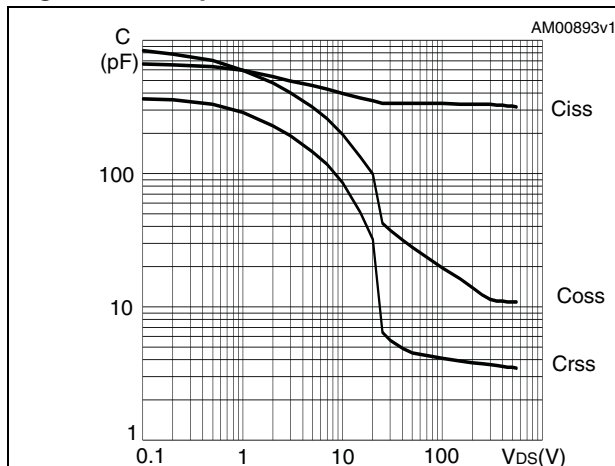


Figure 13. Gate charge vs gate-source voltage

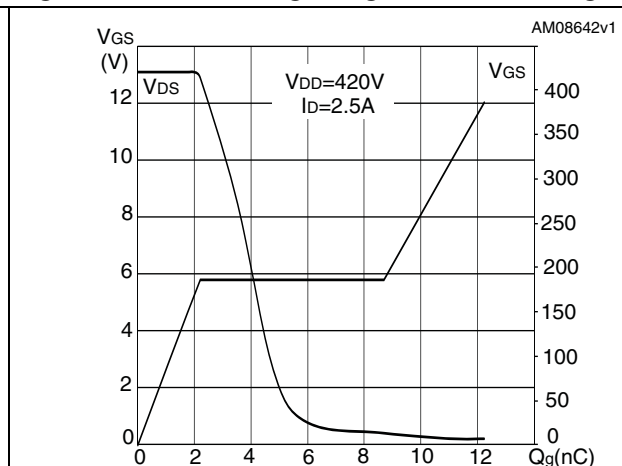


Figure 14. Normalized gate threshold voltage vs temperature

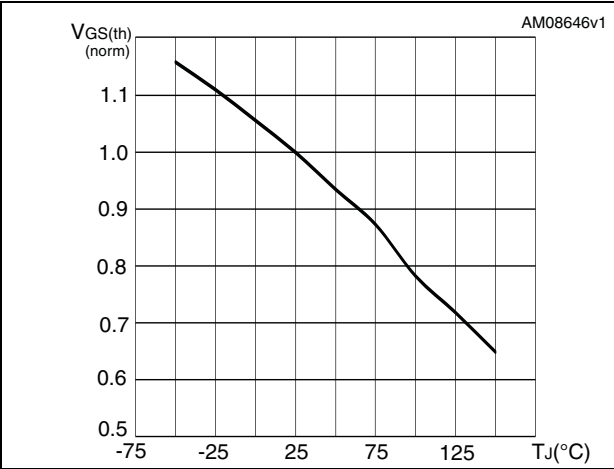


Figure 15. Normalized on resistance vs temperature

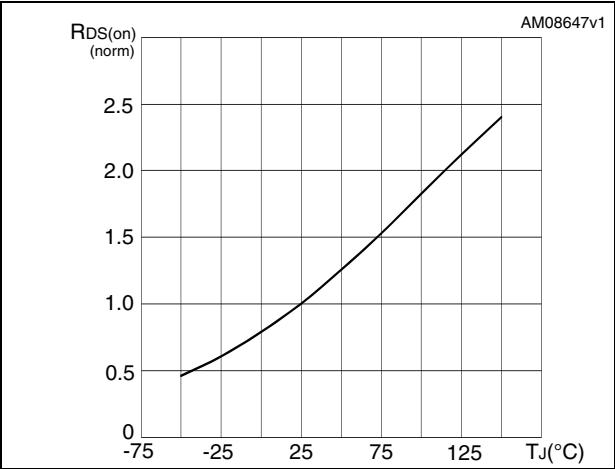


Figure 16. Source-drain diode forward characteristics

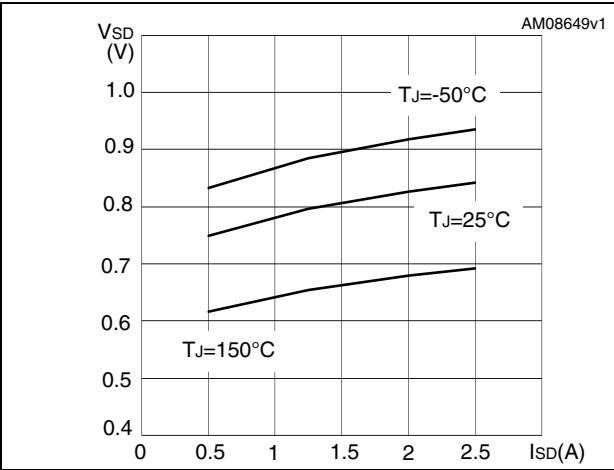
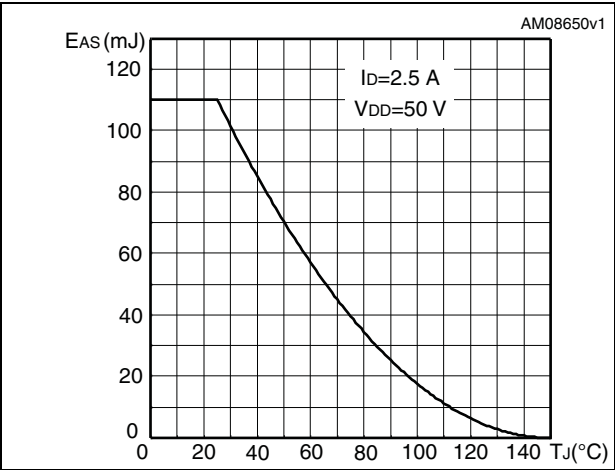


Figure 17. Maximum avalanche energy vs starting TJ



3 Test circuits

Figure 18. Switching times test circuit for resistive load



Figure 19. Gate charge test circuit



Figure 20. Test circuit for inductive load switching and diode recovery times

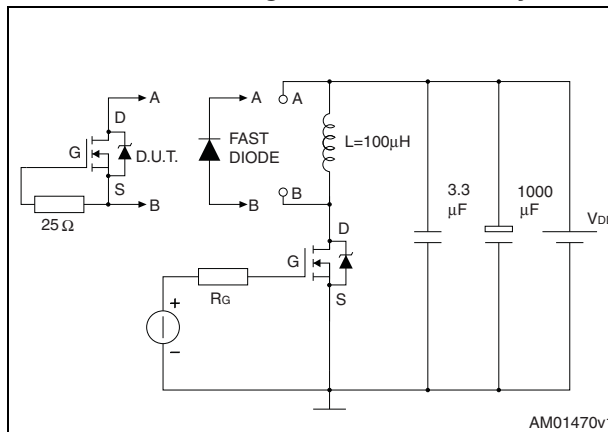


Figure 21. Unclamped Inductive load test circuit



Figure 22. Unclamped inductive waveform

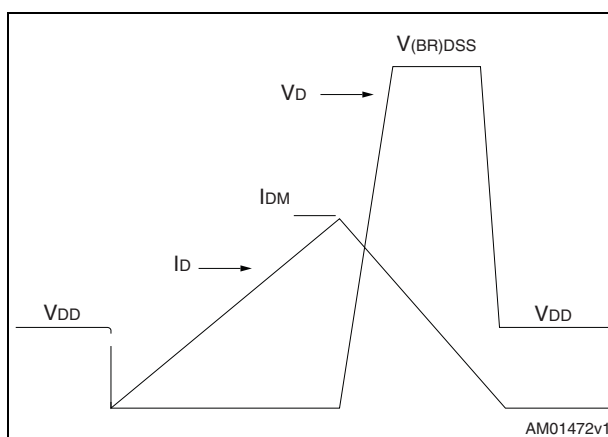
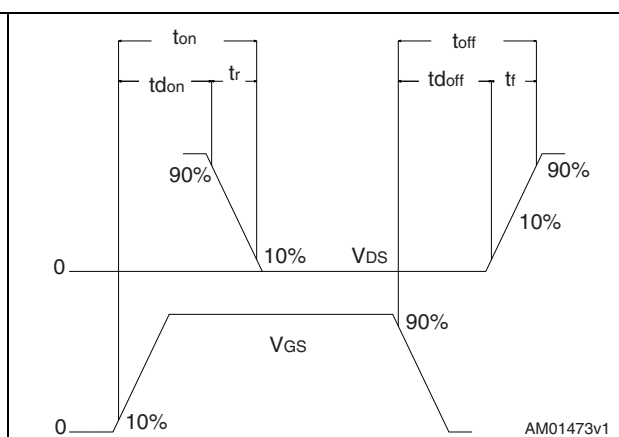


Figure 23. Switching time waveform



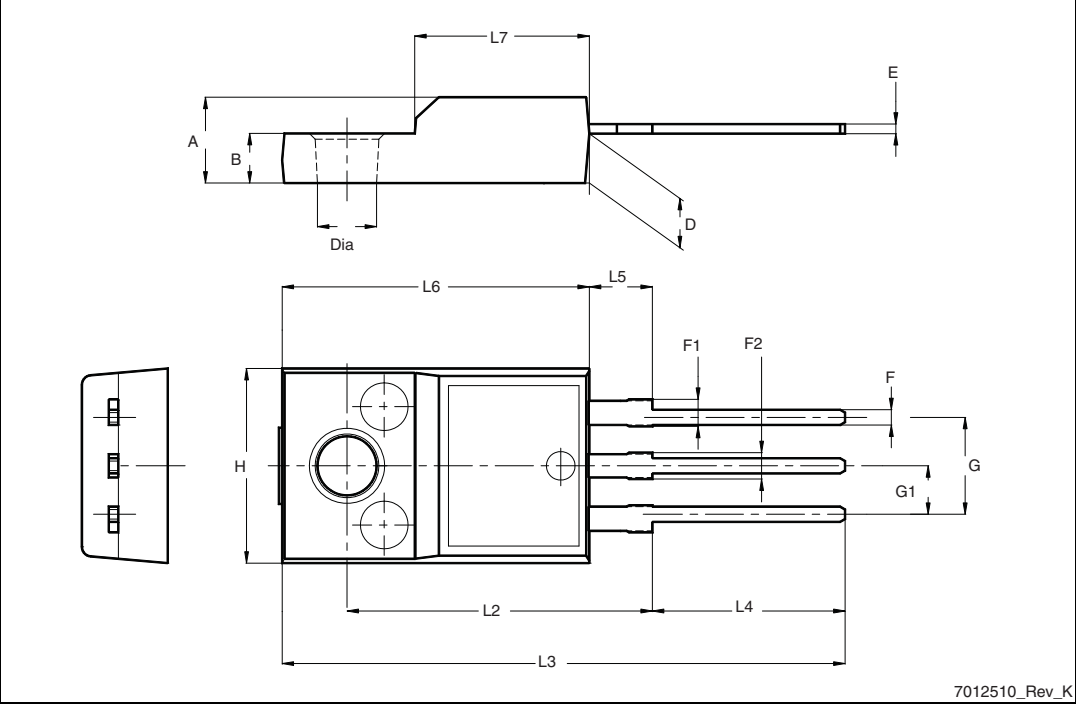
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 9. TO-220FP mechanical data

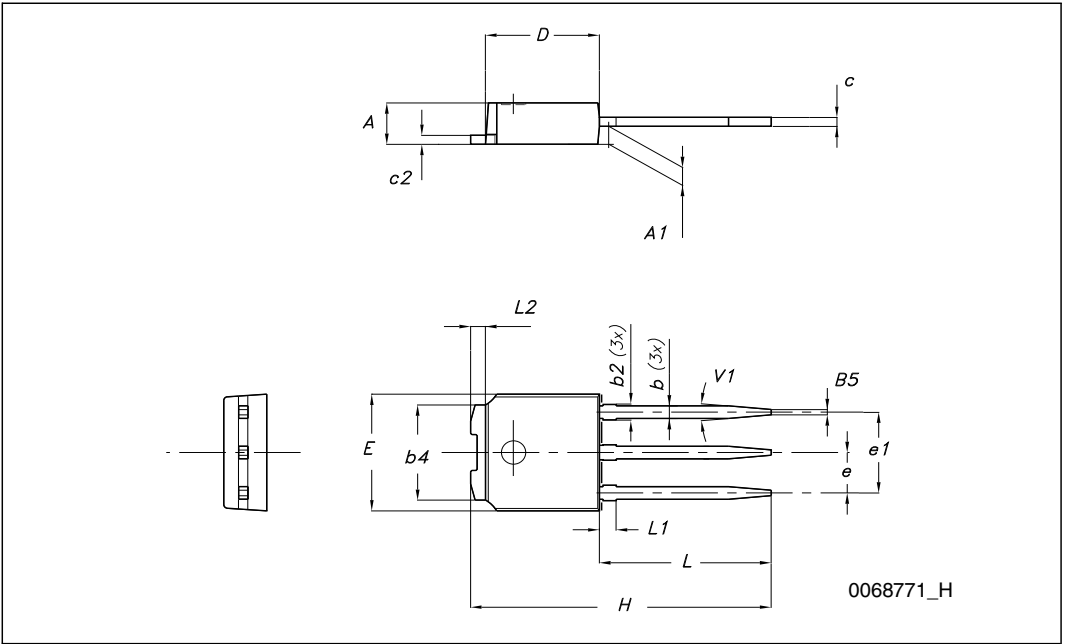
Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 24. TO-220FP drawing



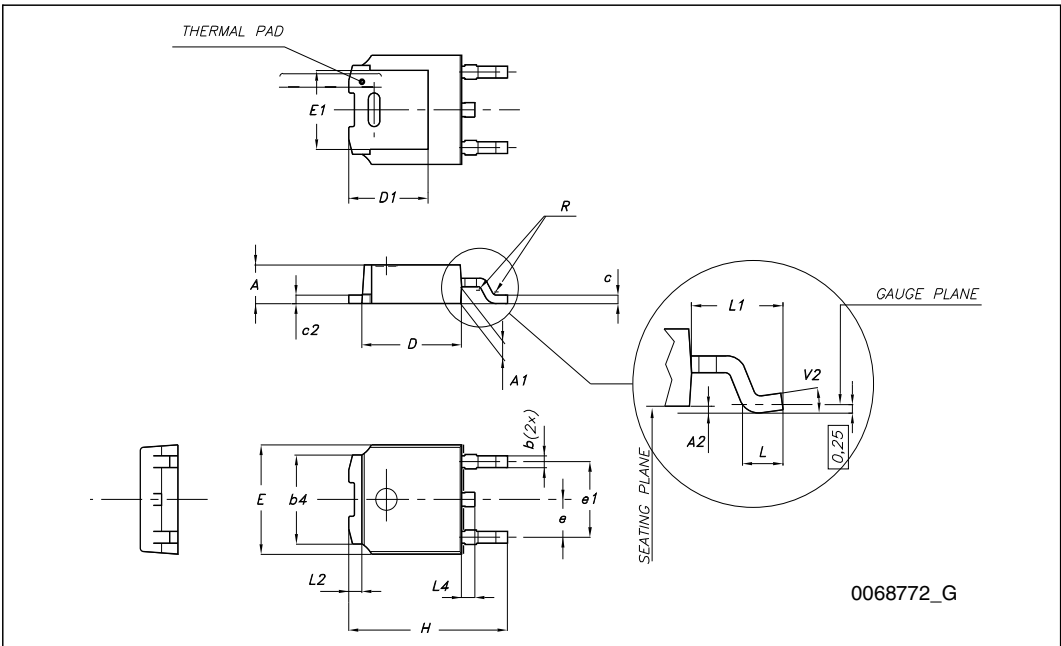
TO-251 (IPAK) mechanical data

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
(L1)	0.80		1.20
L2		0.80	
V1		10 °	



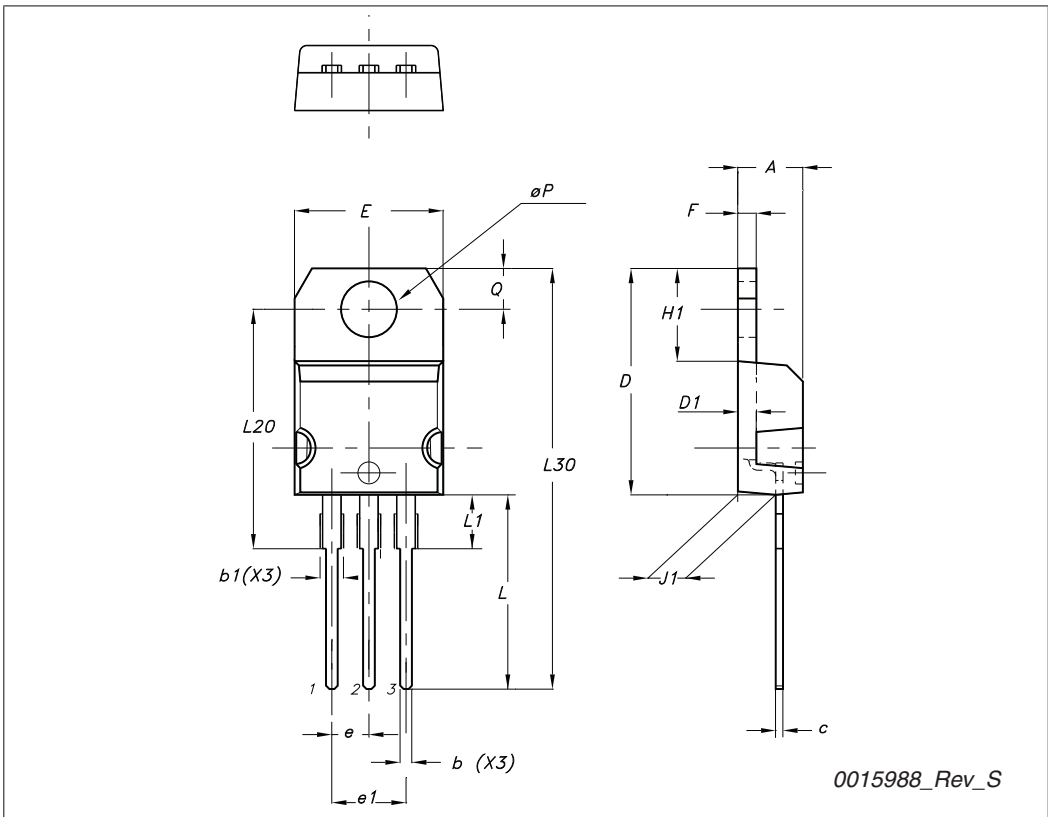
TO-252 (DPAK) mechanical data

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°



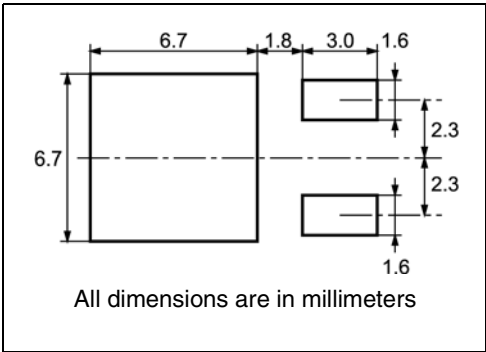
TO-220 type A mechanical data

Dim	mm		
	Min	Typ	Max
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

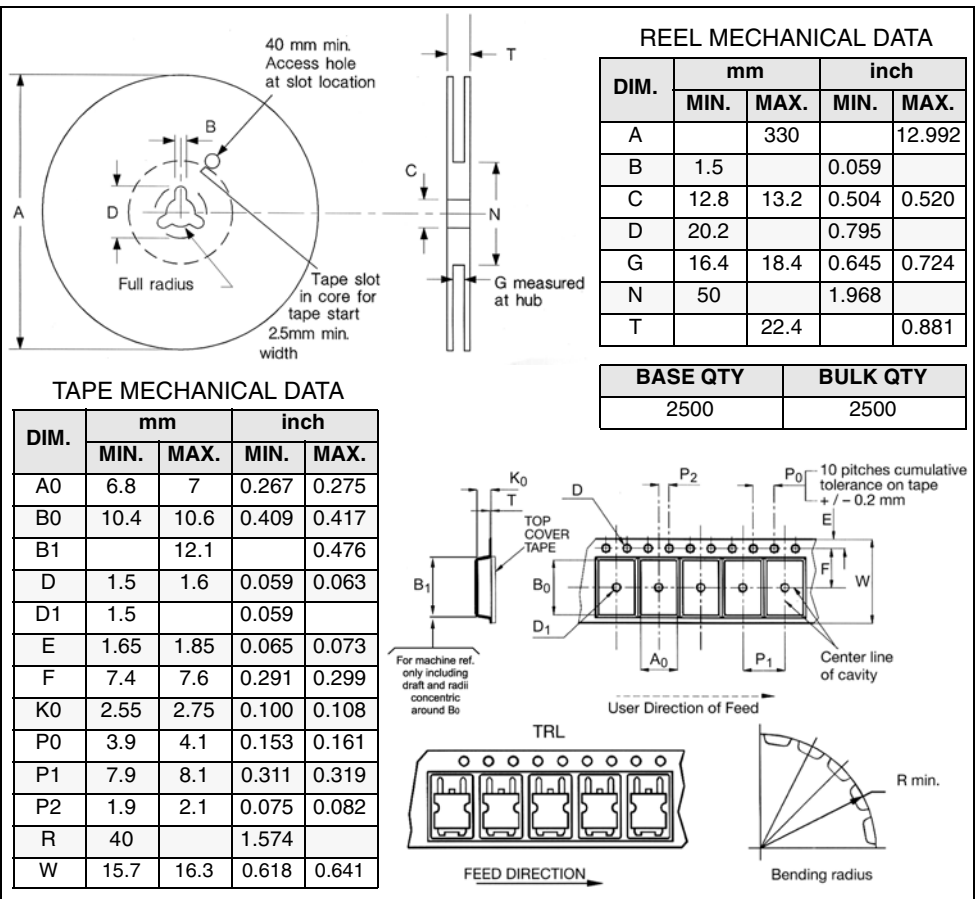


5 Package mechanical data

DPAK FOOTPRINT



TAPE AND REEL SHIPMENT



6 Revision history

Table 10. Document revision history

Date	Revision	Changes
09-Nov-2010	1	First release

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